Product data sheet

1. Product profile

1.1 General description

The KMZ43T is a sensitive magnetic field sensor, employing the magnetoresistive effect of thin-film permalloy. The sensor contains two galvanic separated Wheatstone bridges, at a relative angle of 45° to one another.

A rotating magnetic field in the x-y plane will produce two independent sinusoidal output signals, one a function of $+\cos(2\alpha)$ and the second a function of $+\sin(2\alpha)$, α being the angle between sensor and field direction (see <u>Figure 2</u>). The KMZ43T is suited to high precision angle measurement applications under low field conditions (saturation field strength 25 kA/m).

The sensor can be operated at any frequency between 0 Hz and 1 MHz.

1.2 Features

- Accurate and reliable angle measurement
- Mechanical robustness, contactless principle
- Wear-free operation
- Accuracy independent of mechanical tolerances
- Extended temperature range

1.3 Applications

- Steering angle and torsion
- Headlight adjustment
- Motor positioning

- Window wipers
- Fuel level
- Mirror positioning

1.4 Quick reference data

Table 1. Quick reference data

 T_{amb} = 25 °C and H_{ext} = 25 kA/m; V_{CC} = 5 V; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		<u>[1]</u> _	5	9	V
V_{peak}	peak output voltage	see Figure 2	<u>[1]</u> 60	67	75	mV
V _{offset}	offset voltage	per supply voltage; see <u>Figure 2</u>	<u>[1]</u> –2	-	+2	mV/V
R _{bridge}	bridge resistance		[1][2] 2.7	3.2	3.7	kΩ

^[1] Applicable for bridge 1 and bridge 2.

^[2] Bridge resistance between pin 4 to pin 8, pin 3 to pin 7, pin 1 to pin 5 and pin 2 to pin 6.



Magnetic field sensor

Pinning information 2.

Table 2. **Pinning**

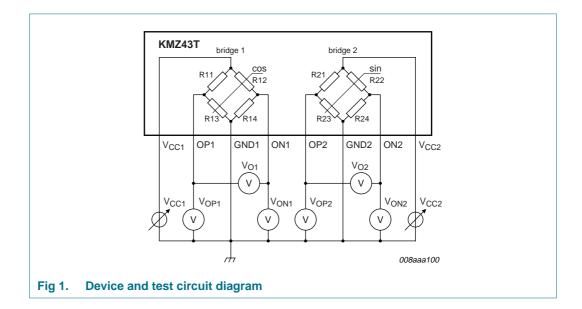
Pin	Symbol	Description	Simplified outline
1	ON1	output voltage bridge 1	
2	ON2	output voltage bridge 2	8 <u>Д Д Д Д</u> 5
3	V_{CC2}	supply voltage bridge 2	
4	V _{CC1}	supply voltage bridge 1	
5	OP1	output voltage bridge 1	1 1 1 1 14
6	OP2	output voltage bridge 2	
7	GND2	ground 2	
8	GND1	ground 1	

Ordering information 3.

Table 3. **Ordering information**

Type number	Packag	Package				
	Name	Description	Version			
KMZ43T	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1			

Circuit diagram



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Magnetic field sensor

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage	<u>[1]</u>	-	9	V
H _{ext}	external magnetic field strength		25	-	kA/m
T _{amb}	ambient temperature		-40	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Applicable for bridge 1 and bridge 2.

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		155	K/W

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7. Characteristics

Table 6. Characteristics

T_{amb} = 25 °C and H_{ext} = 25 kA/m; V_{CC} = 5 V; unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage		<u>[1]</u>	-	5	9	V
V_{peak}	peak output voltage	see Figure 2	<u>[1]</u>	60	67	75	mV
TC _{Vpeak}	temperature coefficient of peak output voltage	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C}$	[1][2]	-0.3	-0.36	-0.42	%/K
R _{bridge}	bridge resistance		[1][3]	2.7	3.2	3.7	kΩ
TC _{Rbridge}	temperature coefficient of bridge resistance	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C}$	[1][4]	0.24	0.26	0.29	%/K
V _{offset}	offset voltage	per supply voltage; see Figure 2	[1]	-2	-	+2	mV/V
TC _{Voffset}	temperature coefficient of offset voltage	per supply voltage; $T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C};$ see Figure 2	[1][5]	-4	-	+4	(μV/V)/K
FH	hysteresis of output voltage	see Figure 3	[1][6]	0	0.05	0.18	%FS
k	amplitude synchronism		<u>[7]</u>	99.5	100	100.5	%
TC_k	temperature coefficient of amplitude synchronism	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +150 ^{\circ}\text{C}$	[8]	-0.01	-	+0.01	%/K
Δα	angular inaccuracy		<u>[9]</u>	0	0.05	0.1	deg

[1] Applicable for bridge 1 and bridge 2.

$$[2] \quad TC_{Vpeak} = 100 \times \frac{V_{peak}(at\ 150\ ^{\circ}C) - V_{peak}(at\ -40\ ^{\circ}C)}{V_{peak}(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[3] Bridge resistance between pin 4 to pin 8, pin 3 to pin 7, pin 1 to pin 5 and pin 2 to pin 6.

[4]
$$TC_{Rbridge} = 100 \times \frac{R_{bridge}(at\ 150\ ^{\circ}C) - R_{bridge}(at\ -40\ ^{\circ}C)}{R_{bridge}(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[5]
$$TC_{Voffset} = \frac{V_{offset}(at\ 150\ ^{\circ}C) - V_{offset}(at\ -40\ ^{\circ}C)}{150\ ^{\circ}C - (-40\ ^{\circ}C)}$$

$$\begin{split} [6] \quad FH_{I} &= 100 \times \left| \frac{V_{OI}(67.5^{\circ})135^{\circ} \!\rightarrow\! 45^{\circ} - V_{OI}(67.5^{\circ})45^{\circ} \!\rightarrow\! 135^{\circ}}{2 \times V_{peak1}} \right| \\ FH_{2} &= 100 \times \left| \frac{V_{O2}(22.5^{\circ})90^{\circ} \!\rightarrow\! 0^{\circ} - V_{O2}(22.5^{\circ})0^{\circ} \!\rightarrow\! 90^{\circ}}{2 \times V_{peak2}} \right| \end{split}$$

[7]
$$k = 100 \times \frac{V_{peak1}}{V_{peak2}}$$

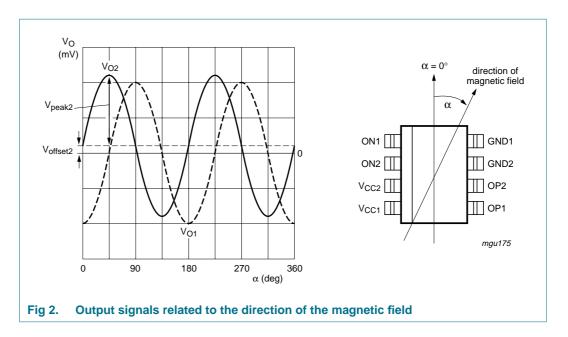
[8]
$$TC_k = 100 \times \frac{k(at\ 150\ ^{\circ}C) - k(at\ -40\ ^{\circ}C)}{k(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

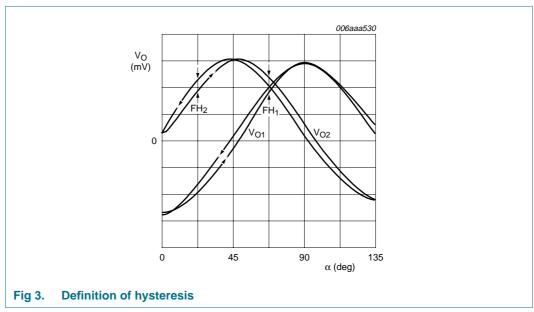
[9] $\Delta \alpha = |\alpha_{real} - \alpha_{meas}|$; $V_{offset} = 0$ V; inaccuracy of angular measurement due to deviations from ideal sinusoidal characteristics, calculated from the third and fifth harmonics of the spectrum V_{O} .

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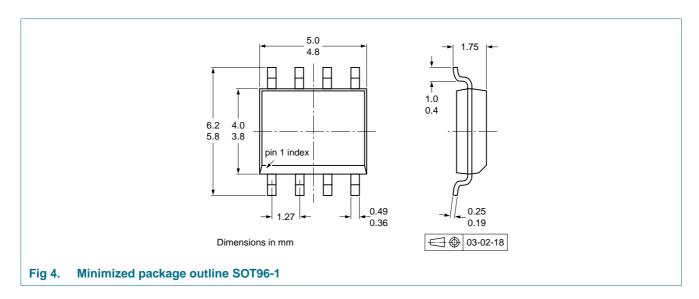


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8. Package outline



9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
KMZ43T_5	20090304	Product data sheet	-	KMZ43T_4
Modifications:	• <u>Table 6</u> : TC	_{Vpeak} and TC _{Rbridge} values ada	pted to 25 °C referer	nce point
KMZ43T_4	20080326	Product data sheet	-	KMZ43T_3
KMZ43T_3	20030915	Product specification	-	KMZ43T_2
KMZ43T_2	20030326	Preliminary specification	-	KMZ43_1
KMZ43_1	20000824	Objective specification	-	-

Magnetic field sensor

10. Legal information

10.1 **Data sheet status**

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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